

Reg. No.:

Name :



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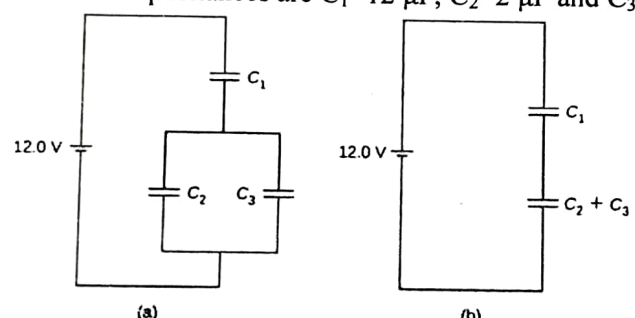
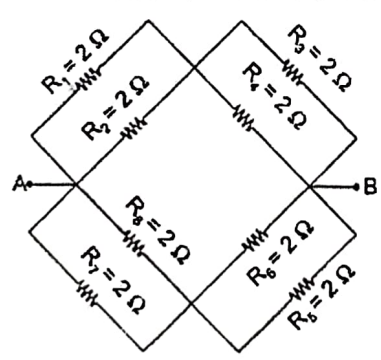
Vellore Institute of Technology

(Deemed to be University under section 3 of UGC Act. 1956)

## Continuous Assessment Test I – January 2023

|           |   |            |   |
|-----------|---|------------|---|
| Programme | : B.Tech                                      | Semester   | : WS 2022-23  |
| Course    | : Basic Electronics                           | Code       | : BECE101L  |
|           |   | Class Nbr  | : CH2022235002756<br>CH2022235002712<br>CH2022235001341 |
| Faculty   | : Dr B Lakshmi, Dr A Prathiba, Mr Premanand S | Slot       | : B2  |
| Time      | : 90 Minutes                                  | Max. Marks | : 50  |

Answer ALL the questions

| Q.No    | Sub-division | Question Text   | Marks           |
|---------|--------------|---|-----------------|
| 1. ✓ i) | n            | <p>Determine the net capacitance <math>C</math> of the capacitor combination shown in Figure 1 a &amp; b when the capacitances are <math>C_1=12\ \mu\text{F}</math>, <math>C_2=2\ \mu\text{F}</math> and <math>C_3=4\ \mu\text{F}</math>.</p>  <p style="text-align: center;">(a) (b)</p> | [3]<br>+<br>[3] |
|         |              | <b>Figure 1</b>   |                 |
| ii)     |              | <p>Find the equivalent resistance across the two ends A and B of this circuit</p>    | [4]             |
|         |              | <b>Figure 2</b>   |                 |
| iii)    |              | Explain the necessity of evolution of electronics since the vacuum tube age to till date.   | [5]             |
| iv)     |              | Compare and contrast between electro-mechanical and solid-state relays.   | [5]             |
| 2. ✓    |              | Discuss the energy-band gap of a semiconductor with a neat diagram.   | [5]             |

|    |      |  |      |
|----|------|--|------|
|    | ii)  | Silicon is doped with $5 \times 10^{16}$ arsenic donor atoms $\text{cm}^{-3}$ .  | [2]  |
|    | (a)  | State whether the material n- or p-type?   | +    |
|    | (b)  | Calculate the electron and hole concentrations at $T = 300 \text{ K}$ . Assume the $n_i$ of silicon as $1.5 \times 10^{10} \text{ cm}^{-3}$  | [3]  |
|    | iii) | A junction diode that has $I_D = 0.3 \text{ mA}$ for $V_D = 0.4 \text{ V}$ . Assume that $\eta = 2$ and $V_T = 0.026 \text{ V}$ . Use the diode equation to compute the diode current at $V_D = 0.65 \text{ V}$ and at $V_D = 0.70 \text{ V}$  | [5]  |
| 3. | i)   | Plot the voltage transfer characteristics $v_O$ versus $v_I$ for a half wave rectifier within the range of $-10 \leq v_I \leq 10 \text{ V}$ . Also sketch $v_O$ versus time for the sinusoidal input. Assume $v_I = 10 \sin \omega t \text{ (V)}$ and $R = 1 \text{ k}\Omega$ .  | [4]  |
|    | ii)  | A full-wave rectifier uses two diodes, the internal resistance of each diode may be assumed constant at $20 \Omega$ . The transformer rms secondary voltage from centre tap to each end of secondary is $50 \text{ V}$ and load resistance is $980 \Omega$ . Compute (i) mean load current (ii) rms value of load current (iii) peak inverse voltage | [6]  |
|    | iii) | Justify how a Zener diode act as a voltage regulator with an appropriate circuit diagram and characteristics   | [5]  |
|    |      | Total Marks  | [50] |



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## Continuous Assessment Test II – March 2023

|           |   |            |   |
|-----------|---|------------|---|
| Programme | : B.Tech                                      | Semester   | : WS 2022-23  |
| Course    | : Basic Electronics                           | Code       | : BECE101L  |
|           |   | Class Nbr  | : CH2022235002756<br>CH2022235002712<br>CH2022235001341 |
| Faculty   | : Dr B Lakshmi, Dr A Prathiba, Mr S Premanand | Slot       | : B2  |
| Time      | : 90 Minutes                                  | Max. Marks | : 50  |

Answer ALL the questions

| Q.No. | Sub-division | Question Text  | Marks |
|-------|--------------|--|-------|
| 1.    | i)           | <p>A npn transistor with <math>\beta = 80</math> is connected in a common-base configuration as shown in Figure 1</p> <p>(a) The emitter is driven by a constant-current source with <math>I_E = 1.2</math> mA. Determine <math>I_B</math>, <math>I_C</math>, <math>\alpha</math>, and <math>V_C</math>.</p> <p>(b) Repeat part (a) for <math>I_E = 0.80</math> mA.</p> <p>(c) Repeat parts (a) and (b) for <math>\beta = 120</math>.</p>                  | 10    |
|       |              | <p>Figure 1</p>  |       |
| 5     | ii)          | <p>Calculate the drain current in an NMOS transistor with parameters <math>V_{TN} = 0.4</math> V, <math>k'_n = 120</math> <math>\mu\text{A}/\text{V}^2</math>, <math>W = 10</math> <math>\mu\text{m}</math>, <math>L = 0.8</math> <math>\mu\text{m}</math>, and with applied voltages of <math>V_{DS} = 0.1</math> V and (a) <math>V_{GS} = 0</math>, (b) <math>V_{GS} = 1</math> V, (c) <math>V_{GS} = 2</math> V, and (d) <math>V_{GS} = 3</math> V.</p> | 5     |
| 24    | ii)          | <p>With a neat circuit diagram and waveform, discuss an electronic circuit which uses positive feedback to produces oscillations at low and medium frequencies. Also mention its frequency of operation</p>  | 5     |
| 5     | iii)         | <p>The tuned oscillator used in the Hartley oscillator of a radio receiver makes use of a LC tuned circuit with <math>L_1 = 50</math> <math>\mu\text{H}</math>, <math>L_2 = 75</math> <math>\mu\text{H}</math> and <math>C = 380</math> pF. Calculate the frequency of oscillation.</p>  | 5     |
| 5     | iii)         | <p>Calculate the drain current and drain-to-source voltage of a common source circuit with an n-channel enhancement-mode MOSFET for Figure 2 if <math>R_1 = 3</math> k<math>\Omega</math>, <math>R_2 = 2</math> k<math>\Omega</math>, <math>R_D = 2</math> <math>\Omega</math>, <math>V_{DD} = 4.7</math> V, <math>V_{TN} = 0.8</math> V, and <math>K_n = 0.2</math> mA/V<sup>2</sup>.</p>   | 5     |

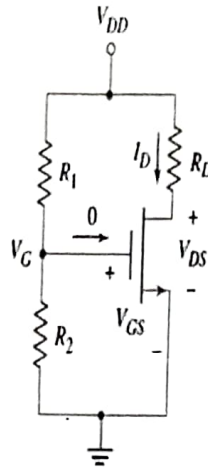


Figure 2

- 25 ✓ i) Convert  $(1110101.1101)_2$  to decimal. 2
- 8 ✓ ii) Realize the functionality of OR, AND and NOT gates using NAND gate only 3
- 5 ✓ iii) Simplify the Boolean expression to a minimum number of literals and implement the same using basic logic gates. 5
- 10 ✓ iv) Implement the Boolean function and also verify the truth table,  $F = xy + x'y' + y'z$  using (a) With AND and inverter gates and (b) With OR and inverter gates. 10
- Total Marks [50]

⇔⇔⇔

$$bc(a+a') + bc'(a+a')$$



**Final Assessment Test (FAT) - APRIL/MAY 2023**

|              |                          |             |                                |
|--------------|--------------------------|-------------|--------------------------------|
| Programme    | <b>B.Tech</b>            | Semester    | <b>Winter Semester 2022-23</b> |
| Course Title | <b>BASIC ELECTRONICS</b> | Course Code | <b>BECE101L</b>                |
| Faculty Name | <b>Prof. PREMANAND S</b> | Slot        | <b>B2</b>                      |
|              |                          | Class Nbr   | <b>CH2022235001341</b>         |
| Time         | <b>3 Hours</b>           | Max. Marks  | <b>100</b>                     |

**SECTION 1 (2 X 4 Marks)**

**Answer All questions**

01. In a common base connection, current amplification factor is 0.9. If the emitter current is 1mA, determine the value of base current. [4]
02. In a common base connection, the emitter current is 1mA. If the emitter circuit is open, the collector current is 50  $\mu$ A. Find the total collector current. Given that  $\alpha = 0.92$ . [4]

**SECTION 2 (10 X 5 Marks)**

**Answer All questions**

03. Calculate the forward bias current of a Si diode when forward bias voltage of 0.4V is applied, the reverse saturation current is  $1.17 \times 10^{-9}$  A and the thermal voltage is 25.2 mV. [5]
04. Explain the working of PN junction under these three operating conditions: [5]
- No bias
  - Forward bias
  - Reverse bias
05. Find the equivalent resistance,  $R_{EQ}$  for the following resistor combination circuit shown in Figure 1. [5]

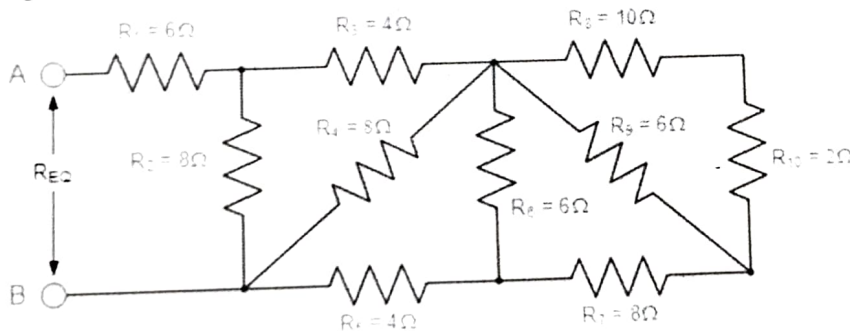


Figure 1

06. Find the total capacitance of the combination of capacitors shown in the figure 2 [5]

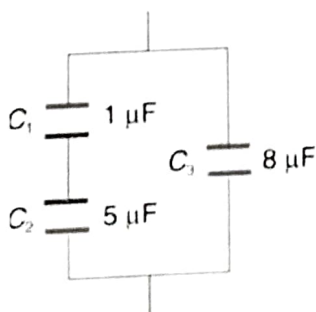


Figure 2



07. Consider an n-channel depletion-mode MOSFET with parameters  $V_{TN} = -1.2 \text{ V}$  and  $k'_n = 120 \mu\text{A/V}^2$ . The drain current is  $I_D = 0.5 \text{ mA}$  at  $V_{GS} = 0$  and  $V_{DS} = 2 \text{ V}$ . Determine the  $W/L$  aspect ratio. [5]
08. Determine the (i) operating frequency and (ii) feedback fraction for Colpitt's oscillator shown in the below Figure 3 [5]

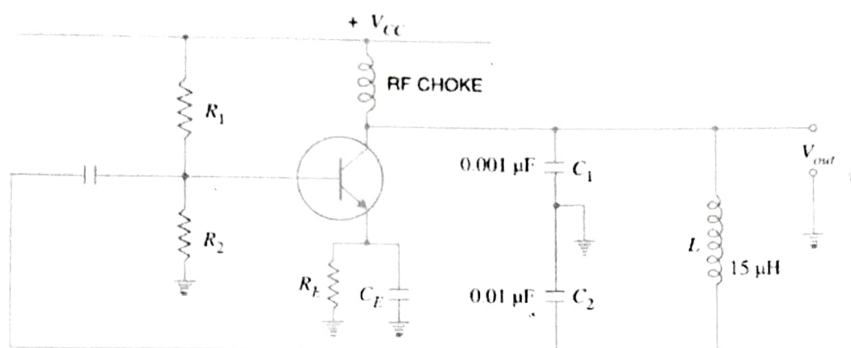


Figure 3

09. In the phase shift oscillator shown for the below figure 4,  $R_1 = R_2 = R_3 = 1 \text{ M}\Omega$  and  $C_1 = C_2 = C_3 = 68 \text{ pF}$ . At what frequency does the circuit oscillate? [5]

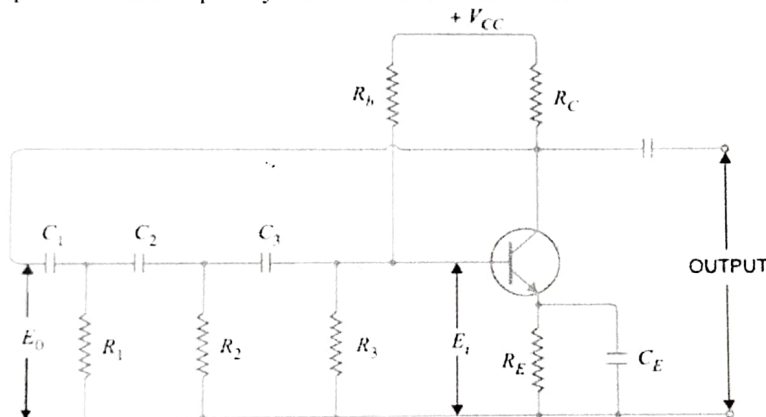


Figure 4

10. A garden contains 39 plants. The following plants were chosen at random, and their heights were recorded in cm: 38, 51, 46, 79, and 57. Calculate their heights' standard deviation. [5]
11. With a suitable and neat sketch, briefly explain a sensor which is used to measure displacement [5]
12. For a certain thermistor  $\beta = 3100 \text{ K}$  and its resistance at  $20^\circ\text{C}$  is known to be  $1050 \Omega$ . The thermistor is used for temperature measurement and the resistance measured is  $2300 \Omega$ . Find the measured temperature if the temperature resistance characteristics of the thermistor is given by  $R = R_0 \exp[\beta((1/T) - (1/T_0))]$  where  $T$  is in Kelvin. [5]

### SECTION 3 (2 X 6 Marks)

#### Answer All questions

13. Describe a simple common-emitter circuit with an npn bipolar transistor and also discuss the relation between collector-emitter voltage and input base current [6]
14. Explain the working of an enhancement n-channel MOSFET with neat schematic for different gate bias and drain bias conditions. Draw the current voltage characteristics and mark the region of operation. [6]

# SECTION 4 (3 X 10 Marks)

Answer All questions

15. Simplify the following Boolean equations

a)  $F = A'B'C' + A'BC' + A'BC + ABC' + ABC$

b)  $\overline{(A + B)\bar{C}\bar{D} + E + \bar{F}}$

16. Represent the output Boolean expression for the logic circuit shown in below figure 5 and simplify the same using Boolean algebra

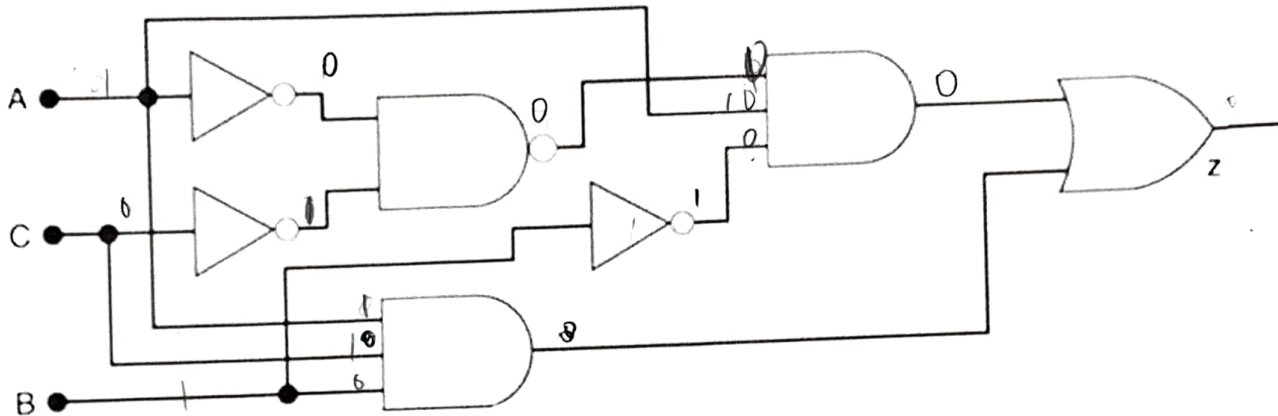
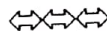


Figure 5

17. Elaborate the functional elements required to complete the task for an instrumentation system using a typical example



**Final Assessment Test (FAT) – June 2022**

|              |                             |             |                                |
|--------------|-----------------------------|-------------|--------------------------------|
| Programme    | <b>B.Tech / M.Tech(Int)</b> | Semester    | <b>Winter Semester 2021-22</b> |
| Course Title | <b>BASIC ELECTRONICS</b>    | Course Code | <b>BECE101L</b>                |
| Faculty Name | <b>Prof. S Selvendran</b>   | Slot        | <b>E2</b>                      |
|              |                             | Class Nbr   | <b>CH2021222300398</b>         |
| Time         | <b>3 Hours</b>              | Max. Marks  | <b>100</b>                     |

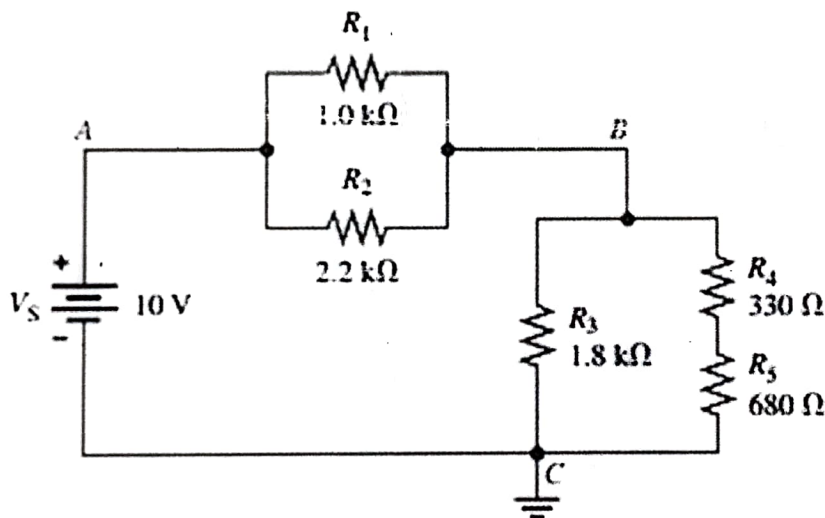
**Section-A (2 X 10 Marks)**

**Answer All questions**

✓ 1. A voltage divider circuit supplies reference voltages to various instruments. From Figure 1. [10]

- ✓ (i) Obtain the voltage drop across AB, voltage drop across  $R_1$ , voltage drop across  $R_2$ , voltage drop across BC, voltage drop across  $R_3$ , voltage drop across  $R_4$ , voltage drop across  $R_5$ .
- ✓ (ii) Determine the total current through the circuit.
- ✓ (iii) What would be the equivalent resistance of the circuit?
- ✓ (iv) What would be the colour coding for  $R_3$  ?

**[10 Marks]**



**Figure 1**

- ✓ 2. a) Discuss in detail about the types of errors that are likely to occur in measuring instruments. [6 Marks] [10]
- b) Consider an analog voltmeter to measure a voltage drop of about 75 V across a resistor. The reading value in the meter is about 73 V. Find i) Absolute Error ii) Relative Error iii) Accuracy iv) Precision value when the mean of measured value is 74.8V. **[4 Marks]**

**Section-B (4 X 15 Marks)**

**Answer All questions**

3. (a) How is the 230V AC input used to charge your mobile phones? What is the type of output? [15]  
 Explain the functionality involved using a suitable diagram. **[12 Marks]**
- (b) How can a diode be used as a rectifier and as a voltage regulator? Give an example for each. **[3 Marks]**



4. (a) For the MOSFET amplifier in common source configuration assume  $V_{DD} = 16V$ ,  $V_D = 6V$ ,  $V_{DS} = 8V$ ,  $I_D = 5mA$  and  $V_{in} = 40V$  with  $1KHz$ . [10 Marks]

Determine

- The value of  $R_D$  and  $R_S$ .
- The value of  $R_2$  if  $R_1 = 150K\Omega$  and  $V_G = 12V$ .
- The value of coupling capacitor whose capacitive impedance should be less than  $2K\Omega$ .
- Draw the circuit diagram.

- (b) For the circuit shown in figure 2, find the frequency of oscillation and feedback fraction. [5 marks]

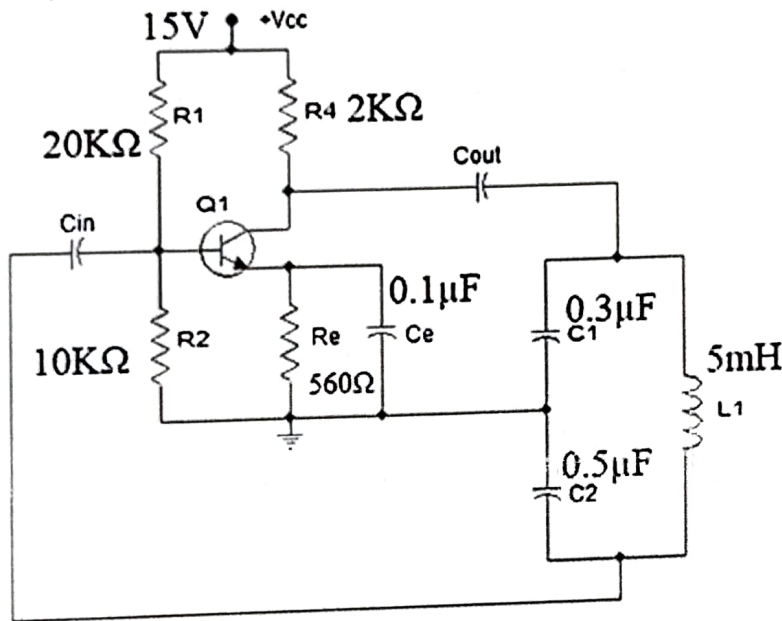


Figure 2

5. a) Convert the decimal number 6781 to Octal and binary number. [4 Marks]
- b) Draw the truth table for the following logic circuit as depicted in figure 3. [3 Marks]

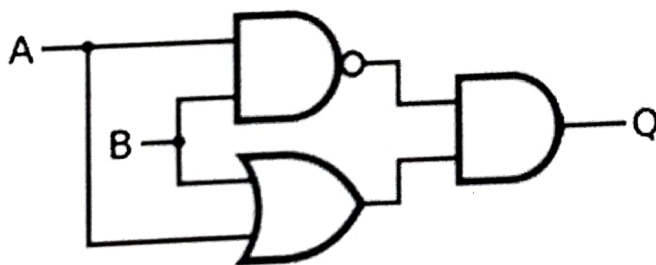


Figure 3

- c) Draw the logic diagram for the Boolean expression  $(x+y)(x+y')+(xy'+x')$ . Also, simplify this expression to minimum possible literals using Boolean algebra. [8 Marks]
6. a) Describe how displacement can be measured using sensor where the displacement variation is converted as change in electrostatic potential variation. Explain with a neat sketch. [8 Marks]
- b) Explain why LVDT is preferable in position sensing over other sensing measurements. [7 Marks]

Section-C (1 X 20 Marks)

Answer All questions

7. a) Sketch and discuss transistor (BJT) configuration which has a (i) **Voltage gain less than or equal to one**, (ii) **Voltage gain greater than one with  $180^\circ$  phase shift**. Mention an application for each. [10 Marks] [20]
- b) Calculate  $I_B$ ,  $I_C$ ,  $I_E$ ,  $V_{BE}$ ,  $V_{CE}$ , and  $V_{CB}$  in the given circuit as shown in figure 4. The transistor has  $\beta_{DC} = 183$ . [10 Marks]

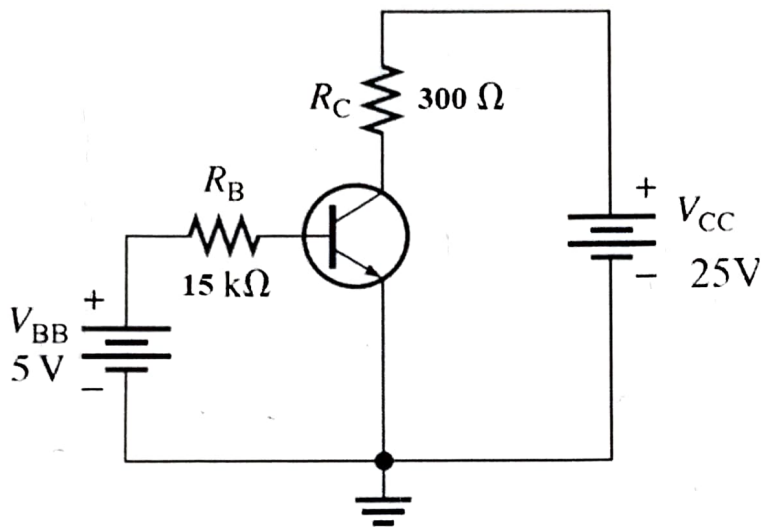


Figure 4

